

TECHNICAL DATA
DATA SHEET 630, REV. C

HERMETIC POWER SCHOTTKY RECTIFIER Very Low Voltage Drop

DESCRIPTION: 45 VOLT, 3.0 AMP, POWER SCHOTTKY RECTIFIER IN A SHD-1/1B PACKAGE.

MAXIMUM RATINGS

ALL RATINGS ARE @ $T_C = 25^\circ\text{C}$ UNLESS OTHERWISE SPECIFIED.

RATING / CONDITION	SYMBOL	MAX.	UNITS
PEAK INVERSE VOLTAGE	PIV	45	Volts
MAXIMUM DC OUTPUT CURRENT (With Cathode Maintained @ $T_C=100^\circ\text{C}$)	I_O	3.0	Amps
MAXIMUM NONREPETITIVE FORWARD SURGE CURRENT ($t=8.3\text{ms}$, Sine)	I_{FSM}	55	Amps
MAXIMUM JUNCTION CAPACITANCE ($V_r=5\text{V}$)	C_T	160	pF
MAXIMUM THERMAL RESISTANCE (Junction to Mounting Surface, Cathode)	$R_{\theta JC}$	7.07	$^\circ\text{C/W}$
MAXIMUM OPERATING AND STORAGE TEMPERATURE RANGE	T_{op}/T_{stg}	-65 to +150	$^\circ\text{C}$

ELECTRICAL CHARACTERISTICS

CHARACTERISTIC			
MAXIMUM FORWARD VOLTAGE DROP, Pulsed ($I_f = 3.0$ Amps) $T_J = 25^\circ\text{C}$ $T_J = 125^\circ\text{C}$	V_f	0.56 0.51	Volts
MAXIMUM REVERSE CURRENT (I_r @ 45V PIV) $T_J = 25^\circ\text{C}$ $T_J = 125^\circ\text{C}$	I_r	0.3 14	mA

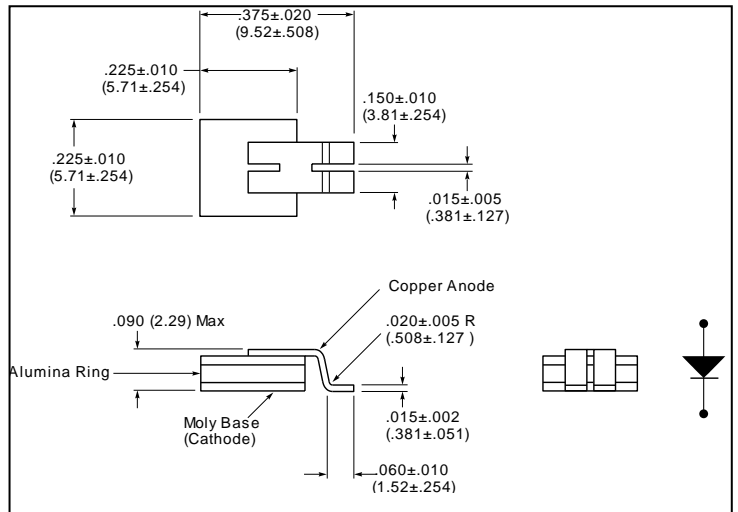
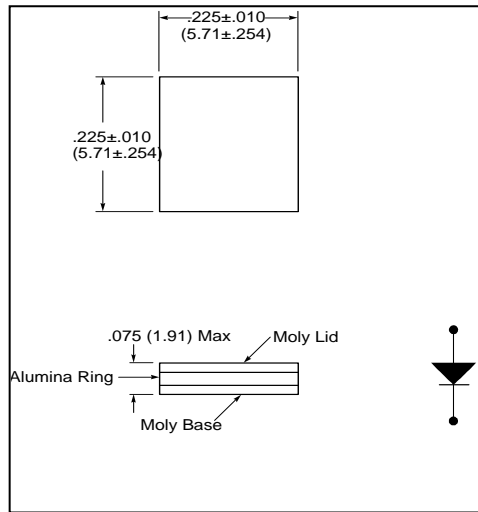
SENSITRON

DATA SHEET 630, REV. C

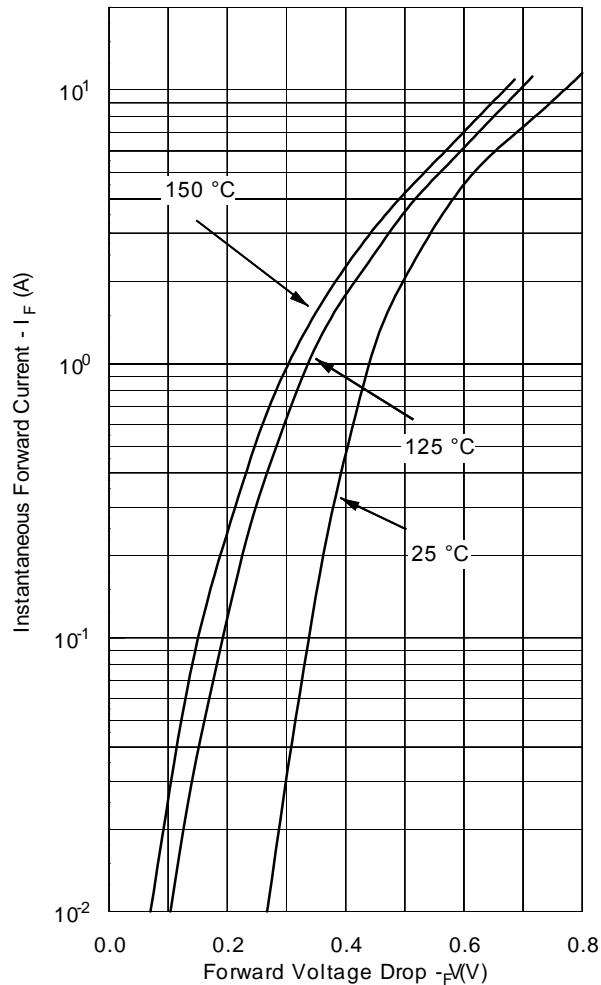
MECHANICAL DIMENSIONS: In Inches / mm

SHD-1B

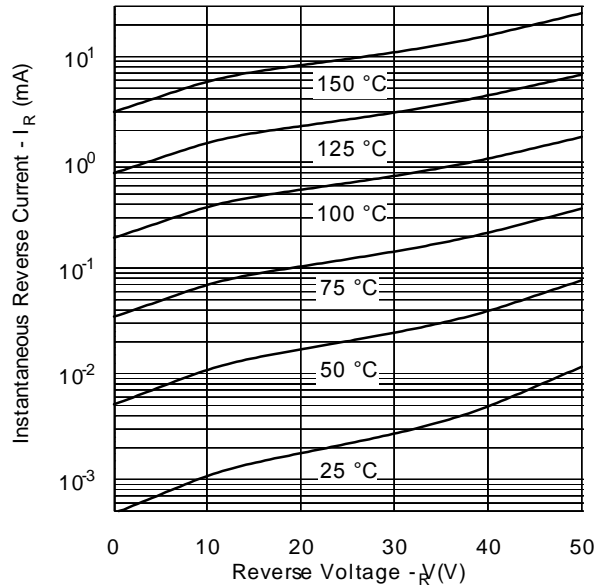
SHD-1



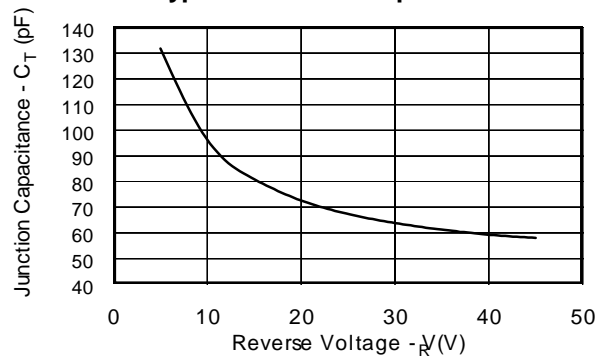
Typical Forward Characteristics



Typical Reverse Characteristics



Typical Junction Capacitance



SENSITRON

DATA SHEET 630, REV.C

DISCLAIMER:

1- The information given herein, including the specifications and dimensions, is subject to change without prior notice to improve product characteristics. Before ordering, purchasers are advised to contact the Sensitron Semiconductor sales department for the latest version of the datasheet(s).

2- In cases where extremely high reliability is required (such as use in nuclear power control, aerospace and aviation, traffic equipment, medical equipment, and safety equipment), safety should be ensured by using semiconductor devices that feature assured safety or by means of users' fail-safe precautions or other arrangement.

3- In no event shall Sensitron Semiconductor be liable for any damages that may result from an accident or any other cause during operation of the user's units according to the datasheet(s). Sensitron Semiconductor assumes no responsibility for any intellectual property claims or any other problems that may result from applications of information, products or circuits described in the datasheets.

4- In no event shall Sensitron Semiconductor be liable for any failure in a semiconductor device or any secondary damage resulting from use at a value exceeding the absolute maximum rating.

5- No license is granted by the datasheet(s) under any patents or other rights of any third party or Sensitron Semiconductor.

6- The datasheet(s) may not be reproduced or duplicated, in any form, in whole or part, without the expressed written permission of Sensitron Semiconductor.

7- The products (technologies) described in the datasheet(s) are not to be provided to any party whose purpose in their application will hinder maintenance of international peace and safety nor are they to be applied to that purpose by their direct purchasers or any third party. When exporting these products (technologies), the necessary procedures are to be taken in accordance with related laws and regulations.